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List of Publications by Year
in descending order

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17	298	840119 11	940134 16
papers	citations	h-index	g-index

17	17	17	359
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High-power low-droop violet semipolar (303Â¯1Â¯) InGaN/GaN light-emitting diodes with thick active layer design. Applied Physics Letters, 2014, 105, .	1.5	55
2	High spatial uniformity of photoluminescence spectra in semipolar (202Â¯1) plane InGaN/GaN quantum wells. Journal of Applied Physics, 2015, 117, 023111.	1.1	27
3	Dynamic characteristics of 410â€‰nm semipolar (202Â¯1Â¯) III-nitride laser diodes with a modulation bandwidth of over 5 GHz. Applied Physics Letters, 2016, 109, .	1.5	27
4	Demonstration of enhanced continuous-wave operation of blue laser diodes on a semipolar 202Â¯1Â¯ GaN substrate using indium-tin-oxide/thin-p-GaN cladding layers. Optics Express, 2018, 26, 1564.	1.7	27
5	Continuous-wave operation of a semipolar InGaN distributed-feedback blue laser diode with a first-order indium tin oxide surface grating. Optics Letters, 2019, 44, 3106.	1.7	24
6	Impact of carrier localization on radiative recombination times in semipolar (202Â¯1) plane InGaN/GaN quantum wells. Applied Physics Letters, 2015, 107, .	1.5	22
7	Measurement and analysis of internal loss and injection efficiency for continuous-wave blue semipolar (202Â¯1Â¯) III-nitride laser diodes with chemically assisted ion beam etched facets. Applied Physics Letters, 2016, 108, .	1.5	21
8	Chemically assisted ion beam etching of laser diode facets on nonpolar and semipolar orientations of GaN. Semiconductor Science and Technology, 2016, 31, 075008.	1.0	18
9	Efficient tunnel junction contacts for high-power semipolar III-nitride edge-emitting laser diodes. Optics Express, 2019, 27, 8327.	1.7	14
10	Semipolar InGaN blue laser diodes with a low optical loss and a high material gain obtained by suppression of carrier accumulation in the p-waveguide region. Japanese Journal of Applied Physics, 2019, 58, 020902.	0.8	13
11	Influence of well width fluctuations on recombination properties in semipolar InGaN quantum wells studied by time- and spatially-resolved near-field photoluminescence. Optical Materials Express, 2017, 7, 3116.	1.6	11
12	Continuous-wave operation of a $(20ar{2}ar{1})$ InGaN laser diode with a photoelectrochemically etched current aperture. Applied Physics Express, 2015, 8, 042701.	1.1	10
13	Compensation effects of high oxygen levels in semipolar AlGaN electron blocking layers and their mitigation via growth optimization. Journal of Crystal Growth, 2019, 507, 118-123.	0.7	8
14	CW operation of highâ€power blue laser diodes with polished facets on semiâ€polar GaN substrates. Electronics Letters, 2016, 52, 2003-2005.	0.5	7
15	Effects of active region design on gain and carrier injection and transport of CW semipolar InGaN laser diodes. Applied Physics Express, 2016, 9, 092104.	1.1	6
16	Properties of near-field photoluminescence in green emitting single and multiple semipolar (202Â¯1) plane InGaN/GaN quantum wells. Optical Materials Express, 2016, 6, 39.	1.6	6
17	Semipolar III-nitride laser diodes for solid-state lighting. , 2019, , .		2